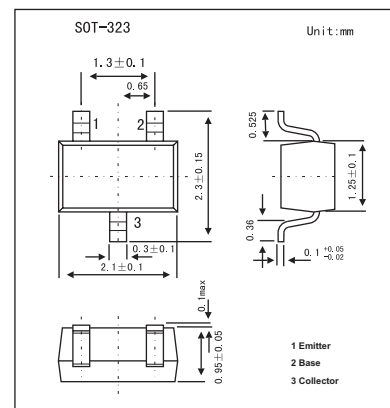


NPN General Purpose Transistor

2PD601AW

■ Features

- High collector current (max. 100 mA)
- Low collector-emitter saturation voltage (max. 500 mV).



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	60	V
Collector-emitter voltage	V_{CE0}	50	V
Emitter-base voltage	V_{EB0}	6	V
Collector current	I_C	100	mA
Peak collector current	I_{CM}	200	mA
Total power dissipation	P_{tot}	200	mW
Storage temperature	T_{stg}	-65 to +150	$^\circ\text{C}$
Junction temperature	T_j	150	$^\circ\text{C}$
Operating ambient temperature	T_{amb}	-65 to +150	$^\circ\text{C}$
Thermal resistance from junction to ambient	$R_{th\ j-a}$	625	K/W

2PD601AW■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I _{CBO}	I _E = 0; V _{CB} = 60 V			10	nA
		I _E = 0; V _{CB} = 60 V; T _j = 150 °C			5	μA
Emitter cut-off current	I _{EBO}	I _C = 0; V _{EB} = 5 V			10	nA
DC current gain 2PD601AQW 2PD601ARW 2PD601ASW	h _{FE}	I _C = 2 mA; V _{CE} = 10 V	160 210 290		260 340 460	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 100 mA; I _B = 10 mA; *			500	mV
Collector capacitance	C _c	I _E = i _e = 0; V _{CB} = 10 V; f = 1 MHz			3.5	pF
Transition frequency 2PD601AQW 2PD601ARW 2PD601ASW	f _T	I _C = 2 mA; V _{CE} = 10 V; f = 100 MHz	100 120 140			MHz

* Pulse test: $t_p \leq 300 \mu\text{s}$; $\delta \leq 0.02$.

■ hFE Classification

TYPE	2PD601AQW	2PD601ARW	2PD601ASW
Marking	6D	6E	6F